

IN THE CLAIMS

Please amend the claims as follows:

The following claim set replaces all prior versions, and listings, of claims in the application:

1. ~~24.~~ (Currently Amended) A method of fabricating an electroluminescent device including the steps of:

B2 a) implanting a surface region of a silicon wafer, doped with a donor impurity to render the wafer n-type, with an acceptor impurity such that the surface region has a volume concentration of the acceptor impurity which is greater than a volume concentration of the donor impurity;

b) anodizing the wafer under illumination to produce a luminescent porous silicon region extending through the surface region; and

c) depositing an electrode on the porous silicon region;

wherein ~~the~~ condition (i) is satisfied, wherein condition (i) requires that at least a part of the region has an acceptor impurity volume concentration comparable with the solid solubility limit of the acceptor impurity in silicon ~~is satisfied;~~

~~and/or~~ and wherein one or more at least one of the following conditions are satisfied:

- (ii) the surface region has a sheet resistivity greater than $100 \Omega \text{ m}^{-1}$ per square immediately prior to the anodizing step;
- (iii) less than 1% of the acceptor impurity is electrically active prior to the anodizing step;
- (iv) the silicon wafer does not receive an anneal between steps (a) and (b); and
- (v) the anodization step (b) causes surface doping of silicon quantum wires within the porous silicon region, rendering the surface doped quantum wires p-type.

B2
CMTD.

2.25. (Currently Amended) A method of fabricating an electroluminescent device according to claim ¹24, wherein, ~~when one or more~~ at least one of conditions (ii) to (v) apply, and the anodization step (b) comprises the step of anodizing the wafer in aqueous hydrofluoric acid in such a manner that microporous porous silicon is formed.

[26-31. (Withdrawn from consideration)]